

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$ Max	$I_D$ $T_C = +25^\circ C$
40V	7.0mΩ @ $V_{GS} = 10V$	110A

## Description and Applications

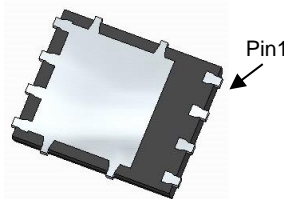
This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

PowerDI5060-8



Top View



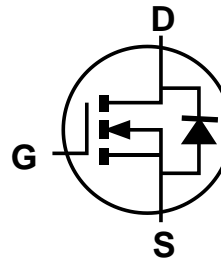
Bottom View

## Features and Benefits

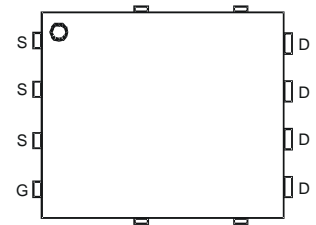
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low  $R_{DS(ON)}$  – Minimizes Power Losses
- Low  $Q_G$  – Minimizes Switching Losses
- <1.1mm Package Profile – Ideal for Thin Applications
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Internal Schematic

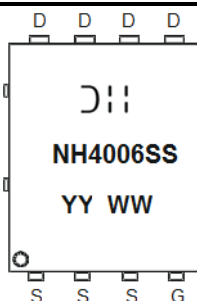

 Top View  
Pin Configuration

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMNH4006SPSQ-13	PowerDI5060-8	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, “Green” and Lead-free.
  3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to [http://www.diodes.com/product\\_compliance\\_definitions.html](http://www.diodes.com/product_compliance_definitions.html)
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



= Manufacturer's Marking  
 NH4006SS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 16 = 2016)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	40	V
Gate-Source Voltage			V <sub>GSS</sub>	20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	Steady State	T <sub>C</sub> = +25°C	I <sub>D</sub>	110	A
		T <sub>C</sub> = +100°C		80	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	180	A
Maximum Continuous Body Diode Forward Current			I <sub>S</sub>	100	A
Avalanche Current (Note 8) L=1mH			I <sub>AS</sub>	64	A
Avalanche Energy (Note 8) L=1mH			E <sub>AS</sub>	208	mJ

**Thermal Characteristics**

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 6)			P <sub>D</sub>	1.6	W
Thermal Resistance, Junction to Ambient (Note 6)		Steady State	R <sub>θJA</sub>	93	°C/W
Total Power Dissipation (Note 7)			P <sub>D</sub>	3.0	W
Thermal Resistance, Junction to Ambient (Note 7)		Steady State	R <sub>θJA</sub>	50	°C/W
Thermal Resistance, Junction to Case			R <sub>θJC</sub>	1.1	
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current, T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 9)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	2.4	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	4.5	7	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 50A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.0A
<b>DYNAMIC CHARACTERISTICS</b> (Note 10)						
Input Capacitance	C <sub>ISS</sub>	—	2,280	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>OSS</sub>	—	557	—	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	283	—	pF	
Gate Resistance	R <sub>G</sub>	—	1.7	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	—	50.9	—	nC	
Gate-Source Charge	Q <sub>GS</sub>	—	9.6	—	nC	V <sub>DS</sub> = 32V, I <sub>D</sub> = 86A
Gate-Drain Charge	Q <sub>GD</sub>	—	20.4	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	7.7	—	ns	
Turn-On Rise Time	t <sub>R</sub>	—	9.3	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 20V, R <sub>G</sub> = 3.5Ω, I <sub>D</sub> = 86A
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	18.1	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	8.1	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	31.6	—	ns	I <sub>F</sub> = 50A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	27.6	—	nC	I <sub>F</sub> = 50A, di/dt = 100A/μs

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

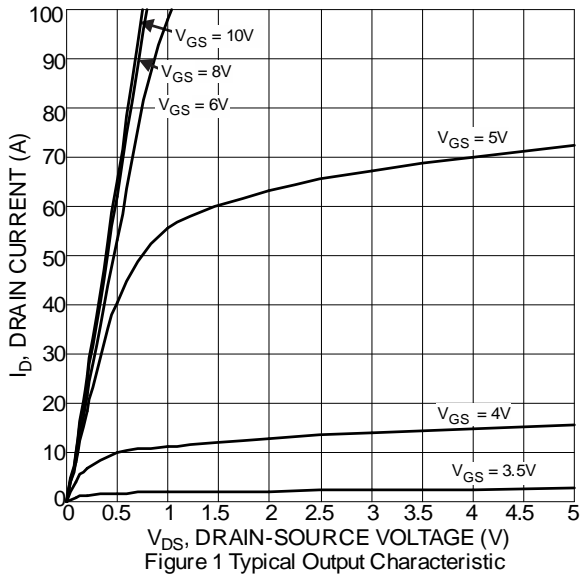


Figure 1 Typical Output Characteristic

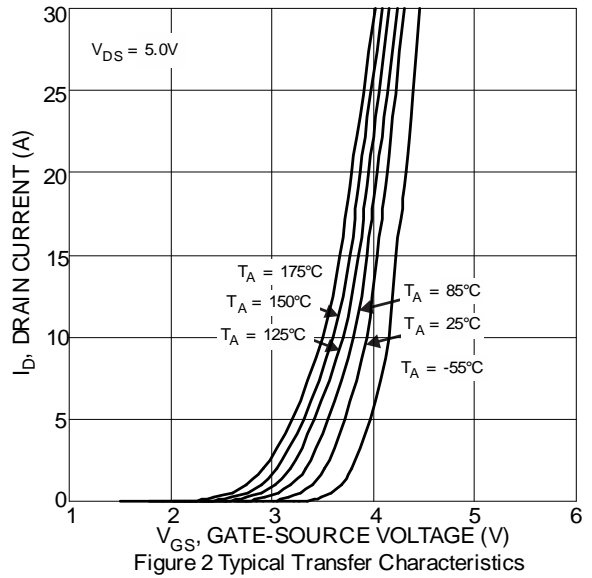


Figure 2 Typical Transfer Characteristics

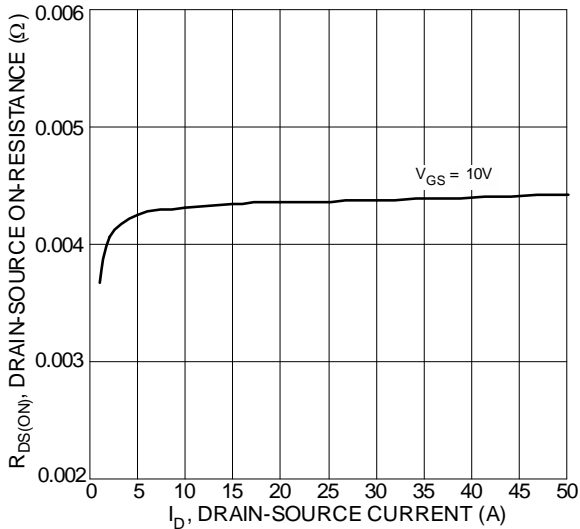


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

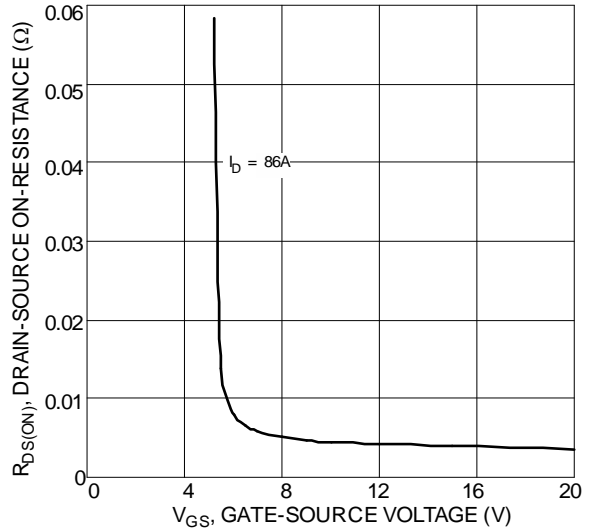


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

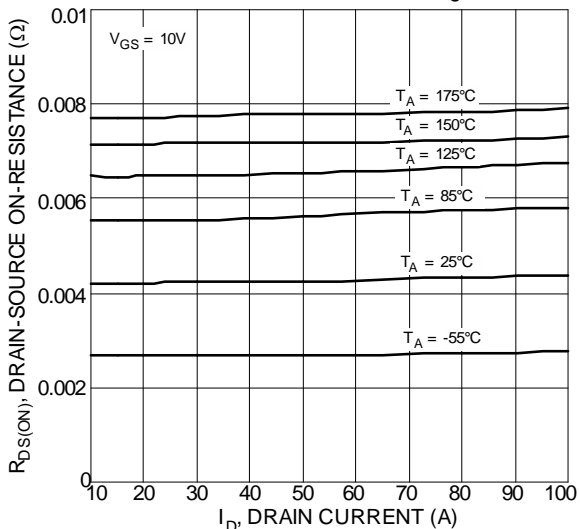


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

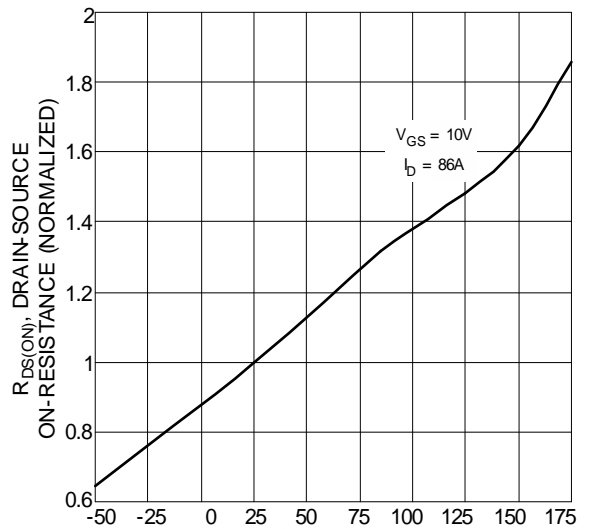


Figure 6 On-Resistance Variation with Temperature

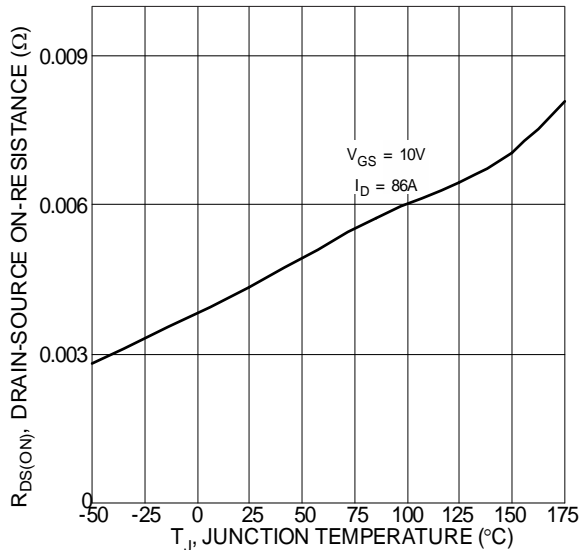


Figure 7 On-Resistance Variation with Temperature

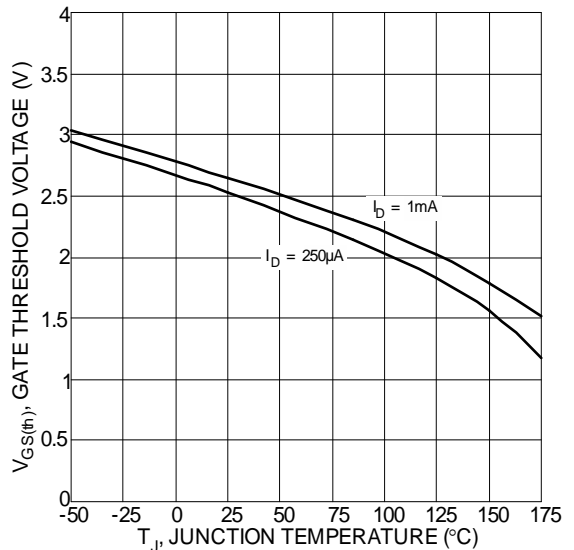


Figure 8 Gate Threshold Variation vs. Ambient Temperature

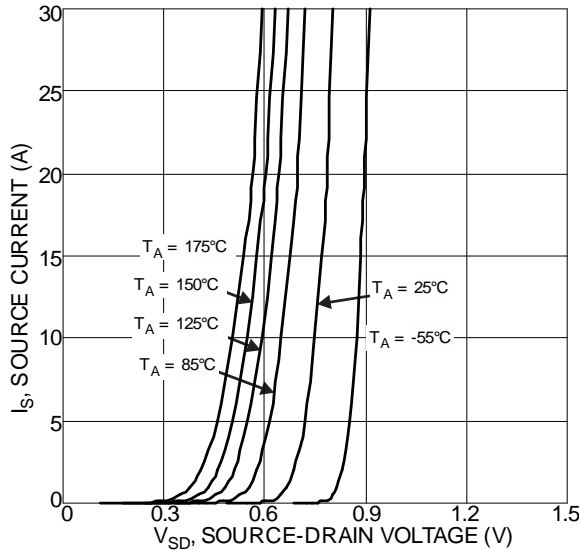


Figure 9 Diode Forward Voltage vs. Current

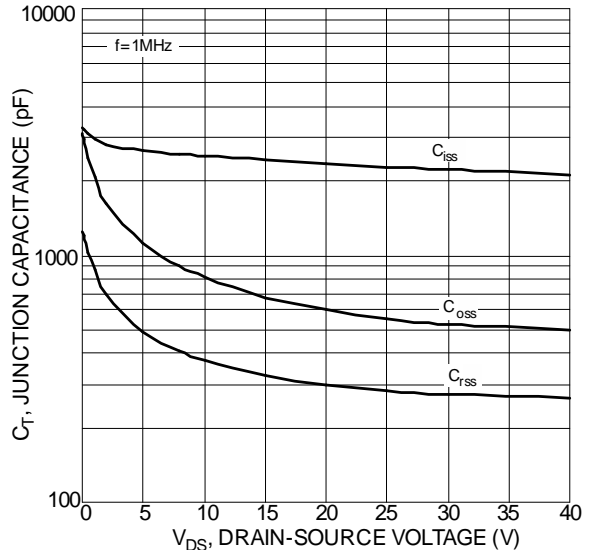


Figure 10 Typical Junction Capacitance

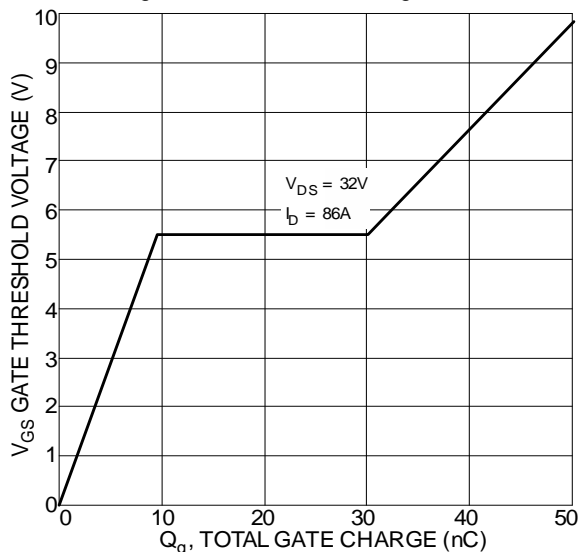


Figure 11 Gate Charge

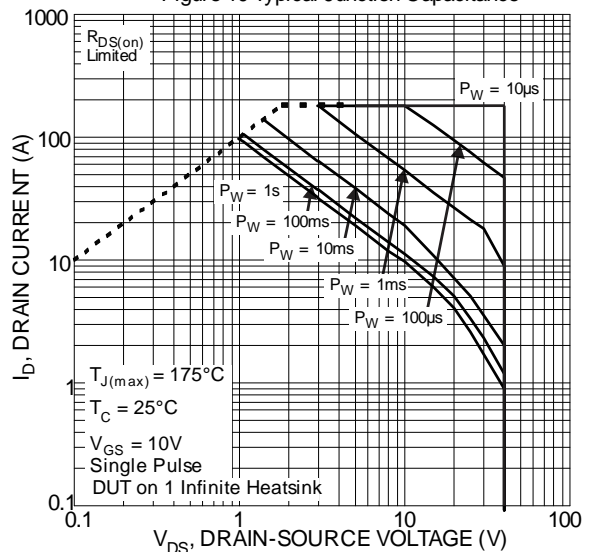
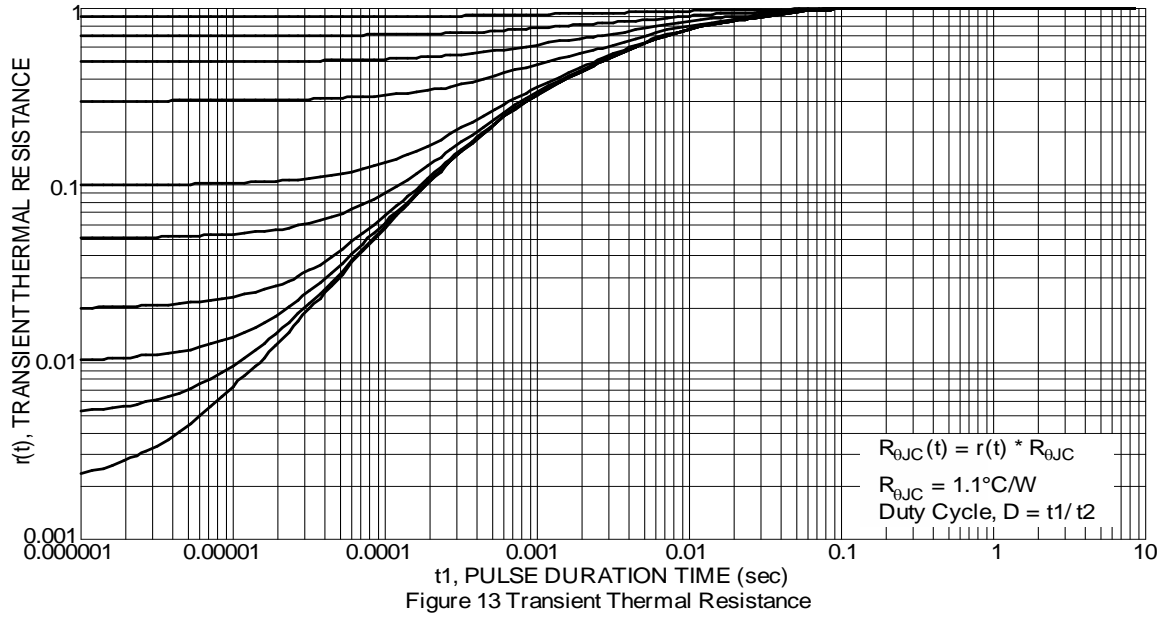


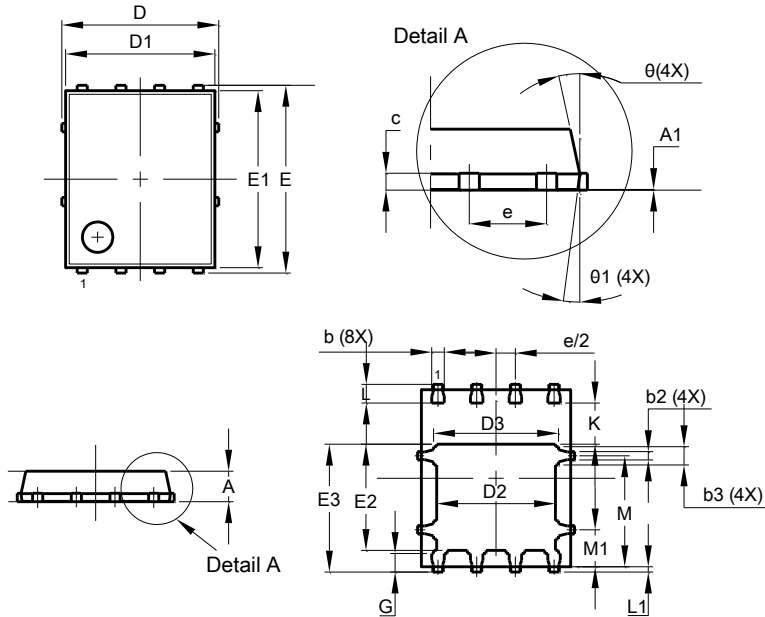
Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8**

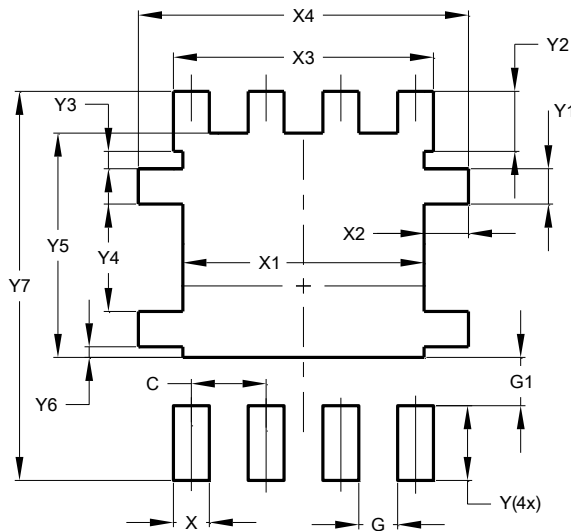


PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
$\theta$	10°	12°	11°
$\theta1$	6°	8°	7°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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